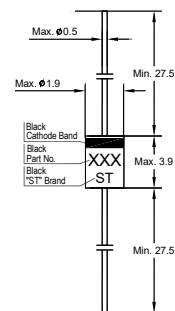


1N914PF, 1N914APF, 1N914BPF

Silicon Epitaxial Planar Switching Diode

Features

- Lead Free
- Fast switching speed
- High reliability



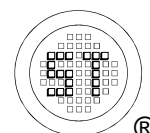
Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current 1N914PF 1N914APF / 1N914BPF	$I_{F(AV)}$	75 200	mA
Forward Continuous Current 1N914PF 1N914APF / 1N914BPF	I_{FM}	150 300	mA
Non-Repetitive Peak Forward Surge Current at $t = 1$ s 1N914PF at $t = 1$ μs 1N914APF / 1N914BPF at $t = 1$ μs	I_{FSM}	1 1 4	A
Power Dissipation	P_{tot}	500	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 175	$^\circ\text{C}$

Thermal Characteristics

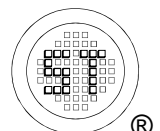
Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	300	$^\circ\text{C/W}$



1N914PF, 1N914APF, 1N914BPF

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 100\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 20\text{ mA}$	V_F	0.62 - - -	0.72 1 1 1	V
Reverse Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$, $T_J = 150\text{ }^{\circ}\text{C}$	I_R	- - -	25 5 50	nA μA μA
Diode Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_j	-	4	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$, $I_{rr} = 1\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\text{ }\Omega$	t_{rr}	-	4	ns



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Electrical Characteristics Curves

